



DMT3020LDV

DUAL 30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UXC)

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C		
001/	20mΩ @ V _{GS} = 10V	32A		
30V	$32m\Omega @ V_{GS} = 4.5V$	25A		

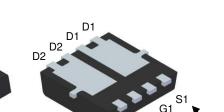
Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- Analog Switch

PowerDI3333-8 (Type UXC)



Bottom View

G2 S2

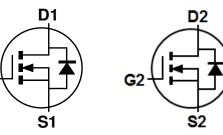


- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

G1

- Case: PowerDI[®]3333-8 (Type UXC)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)



Equivalent Circuit

Ordering Information (Note 4)

Top View

	Part Number	Case	Packaging	
	DMT3020LDV-7	PowerDI3333-8 (Type UXC)	2,000/Tape & Reel	
DMT3020LDV-13 PowerDI3333-8 (Type UXC) 3,000/Tape & Reel				
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.				

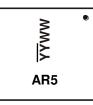
Pin 1

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\begin{array}{l} AR5 = \mbox{Product Type Marking Code} \\ \hline \hline YYWW = \mbox{Date Code Marking} \\ \hline YY = \mbox{Last Two Digits of Year (ex: 18 for 2018)} \\ WW = \mbox{Week Code (01 to 53)} \end{array}$



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current, V_{GS} = 10V (Note 7)	Steady State	T _C = +25°C T _C = +70°C	۱ _D	32 25	А
Maximum Body Diode Forward Current (Note 7)		Is	25	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	50	A		
Pulsed Drain Body Diode Forward Current (10µs Pu	I _{SM}	50	A		
Avalanche Current (L = 0.1mH) (Note 8)			IAS	13	А
Avalanche Energy (L = 0.1mH) (Note 8)			E _{AS}	8.5	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	138	°C/W
Total Power Dissipation (Note 6)		PD	1.9	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{\theta JA}$	67	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _{0JC}	4.8	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	30.0		—	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1.0	μA	$V_{DS}=24V,V_{GS}=0V$	
Gate-Source Leakage	I _{GSS}	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			14	20	mΩ	$V_{GS} = 10V, I_D = 9.0A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	22	32	11122	$V_{GS} = 4.5V, I_D = 7.0A$	
Diode Forward Voltage	V _{SD}		8.0	1.2	V	$V_{GS} = 0V, I_{S} = 2A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	-	393	_	pF		
Output Capacitance	Coss	_	173	—	рF	− V _{DS} = 15V, V _{GS} = 0V, − f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	27	_	pF	1 = 1.00012	
Gate Resistance	Rg	Ι	1.1		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	Ι	7.0		nC		
Total Gate Charge (V _{GS} = 4.5V)	Qg		3.6	_	nC		
Gate-Source Charge	Q _{gs}	—	0.9	—	nC	$V_{DD} = 15V, I_D = 9A$	
Gate-Drain Charge	Q _{gd}	—	1.5	—	nC		
Turn-On Delay Time	t _{D(ON)}		1.8	_	ns		
Turn-On Rise Time	t _R	—	1.9	—	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	—	7.5	—	ns	$R_G = 6\Omega, I_D = 9A$	
Turn-Off Fall Time	tF	_	2.4	_	ns	7	
Reverse Recovery Time	t _{RR}	—	10	—	ns	I _F = 9A, dl/dt = 100A/µs	
Reverse Recovery Charge	Q _{RR}	_	2.6	_	nC		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).

8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

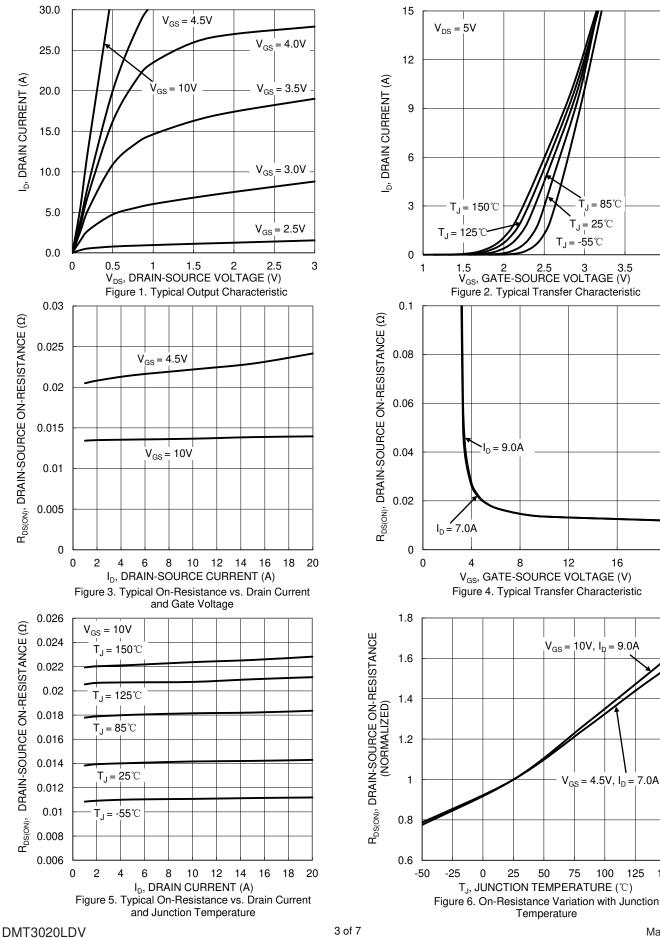


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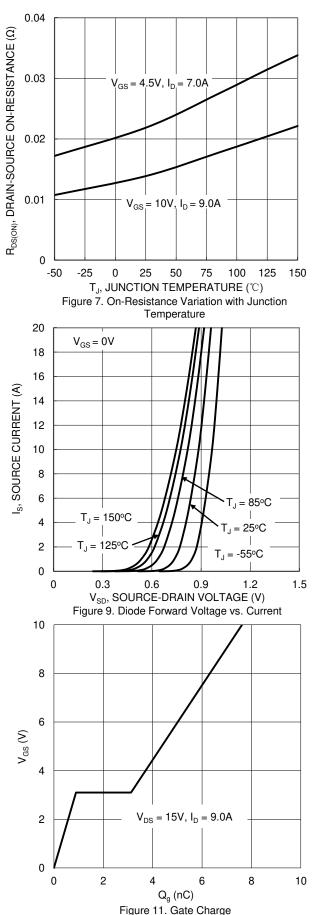
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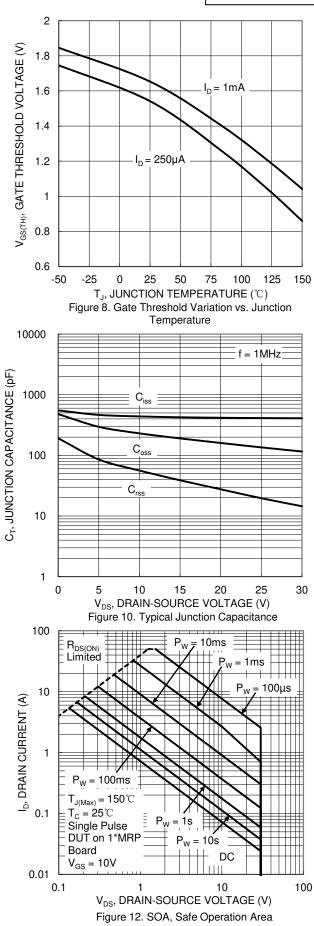
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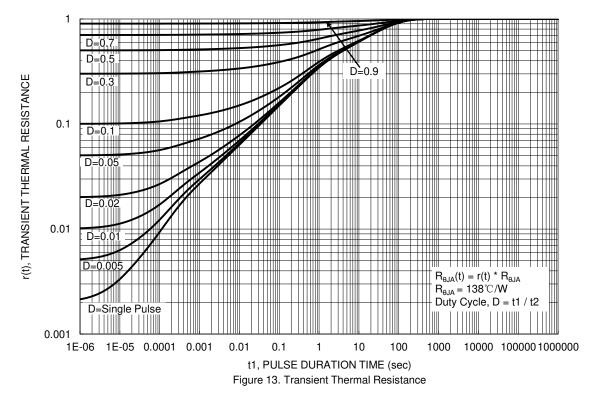






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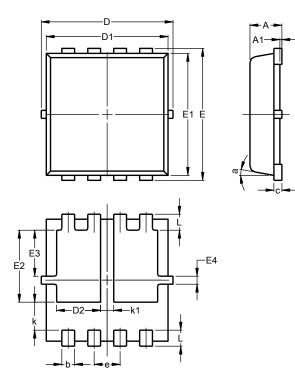




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UXC)

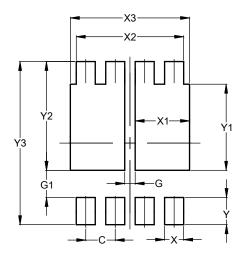


PowerDI3333-8						
(Type UXC)						
Dim Min Max Typ						
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	0.90	1.30	1.10			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
L	0.30	0.50	0.40			
k	0.50	0.90	0.70			
k1	0.13	0.53	0.33			
а	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UXC)



Dimensions	Value (in mm)
С	0.650
G	0.230
G1	0.600
Х	0.420
X1	1.200
X2	2.370
X3	2.630
Y	0.600
Y1	1.900
Y2	2.400
Y3	3.600



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